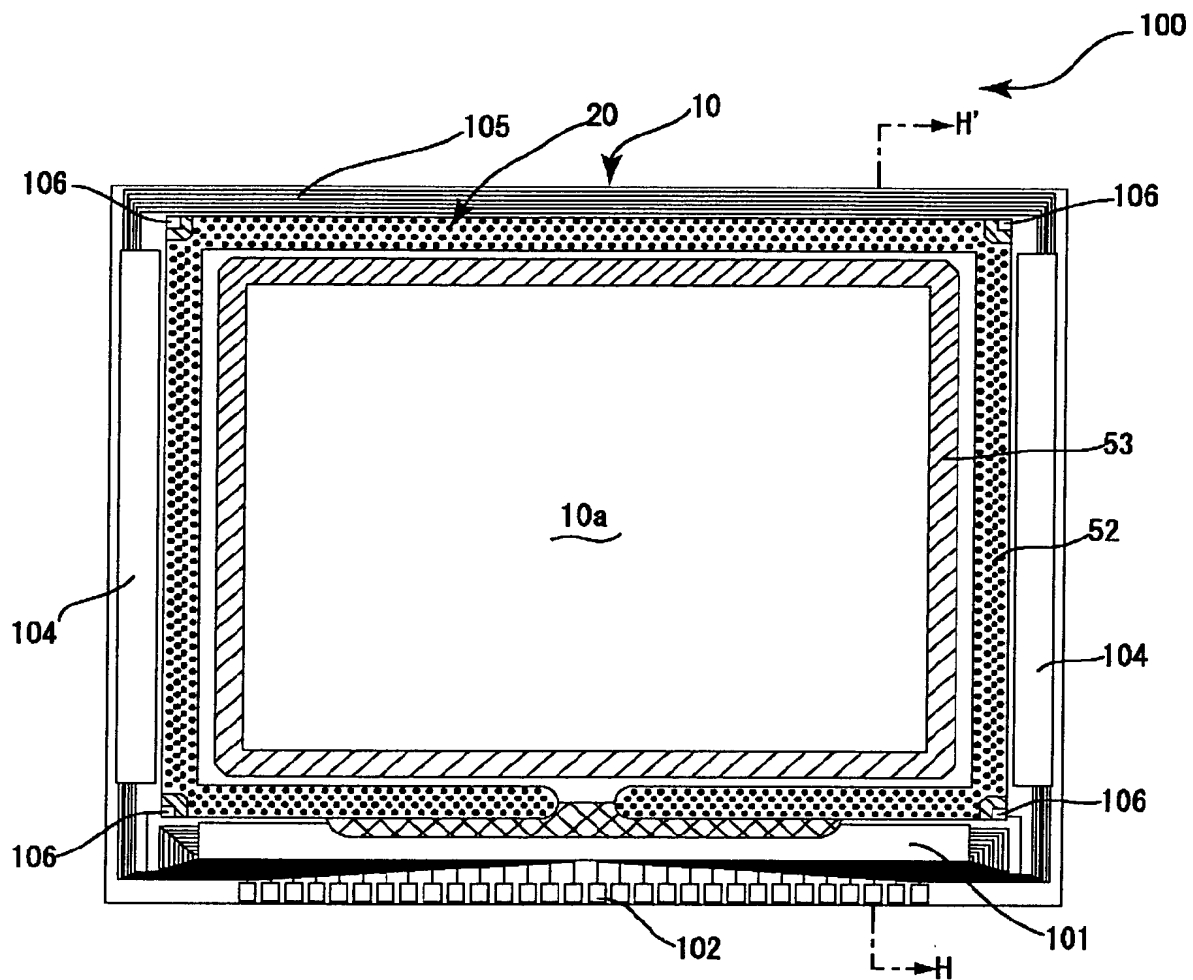
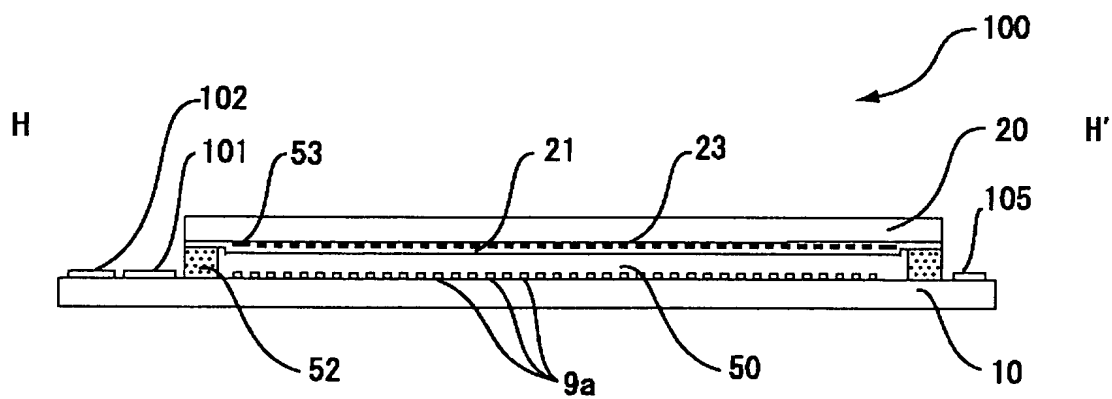


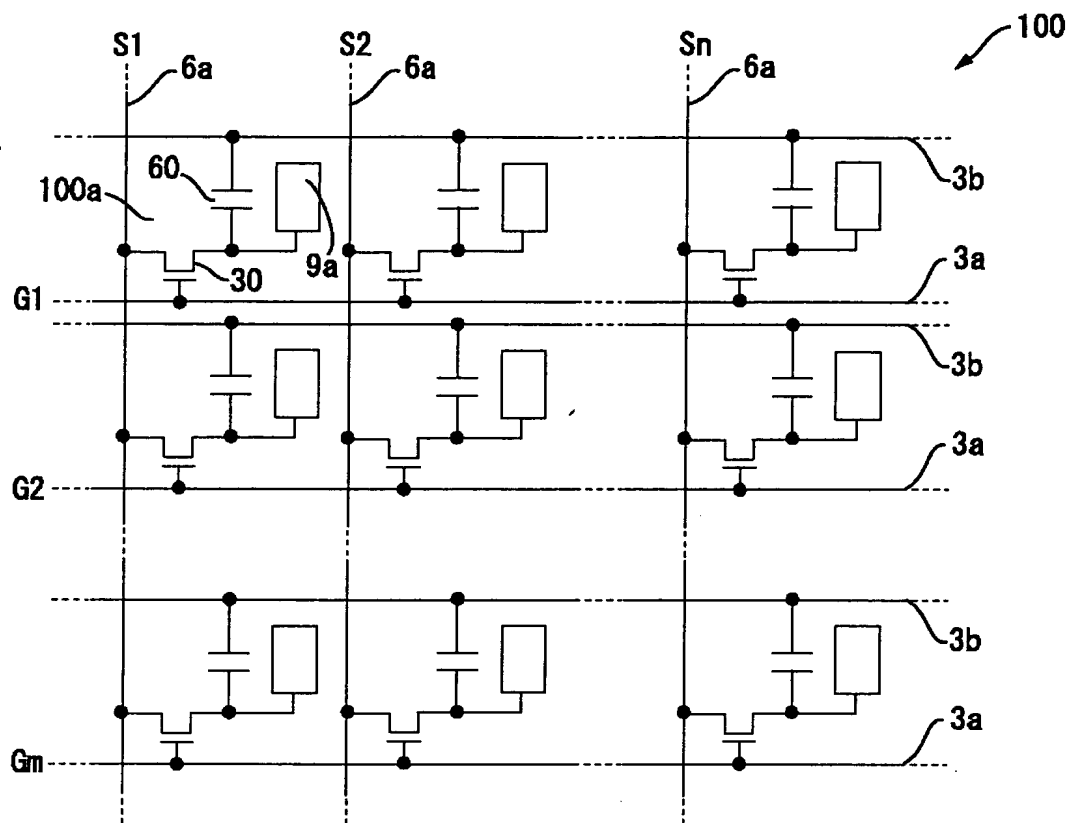
【FIG. 1】



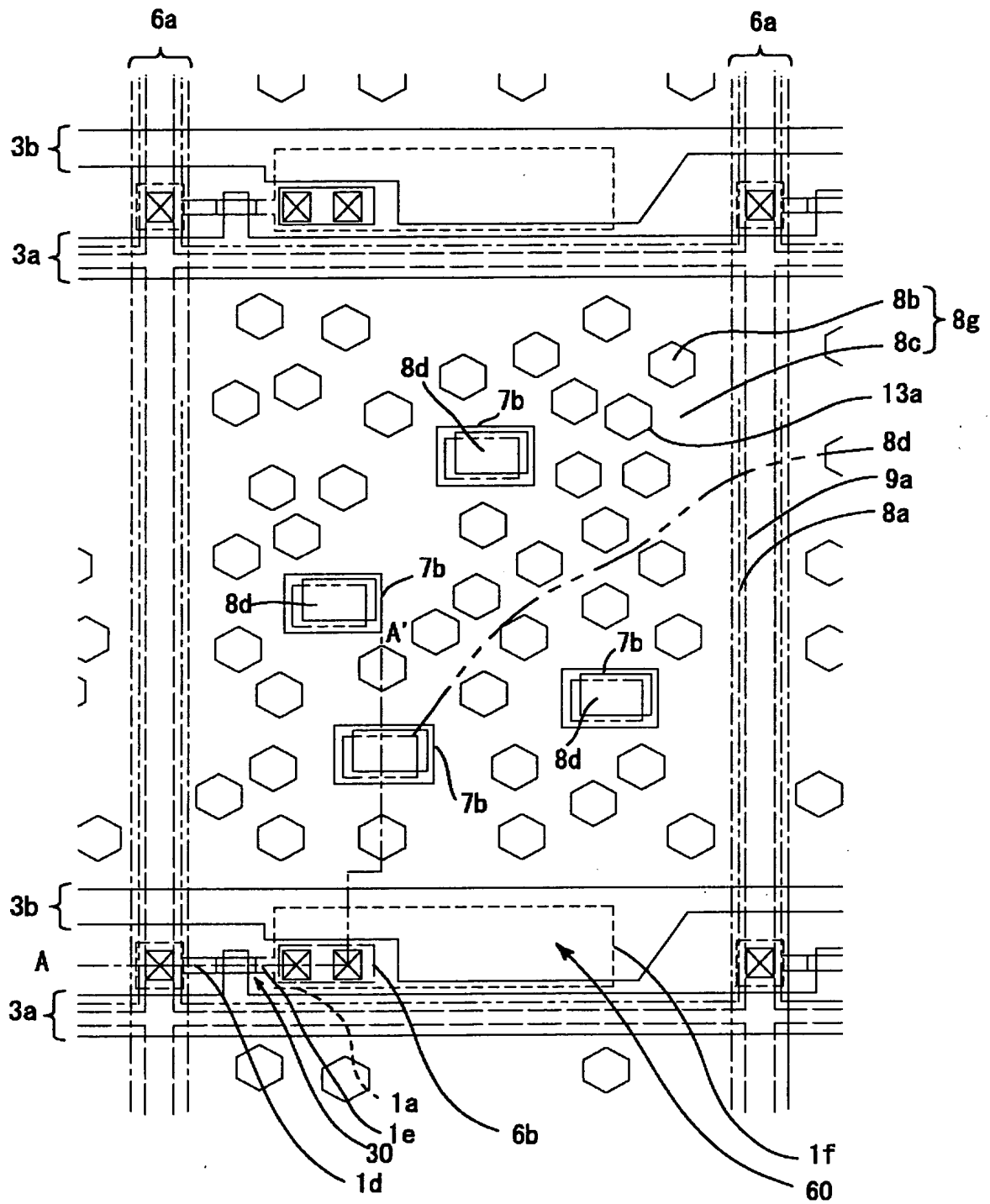
【FIG. 2】



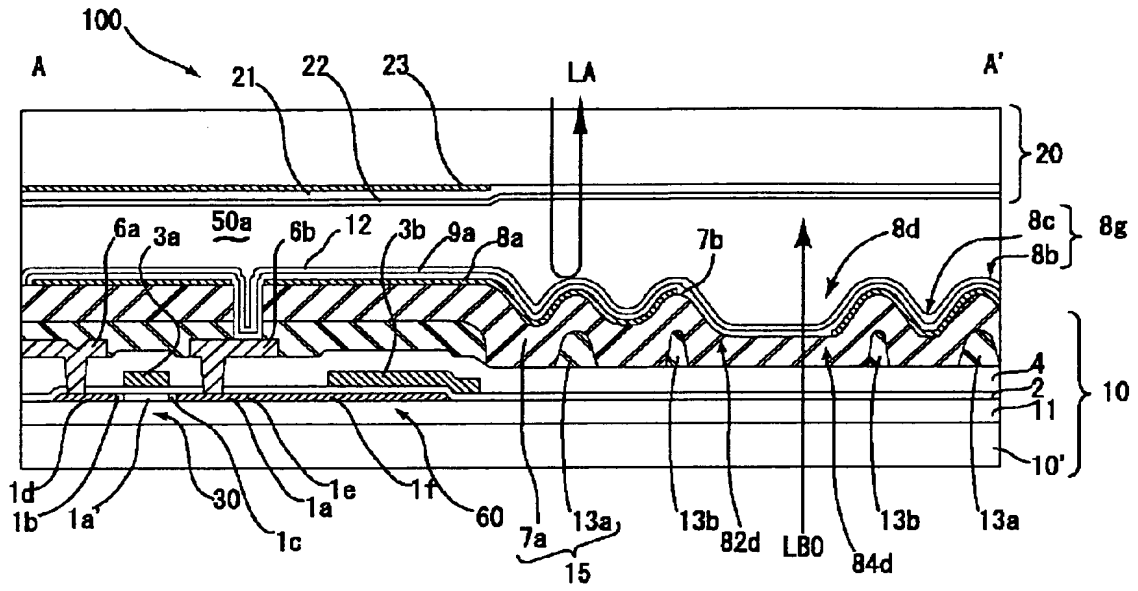
【F I G. 3】



【FIG. 4】

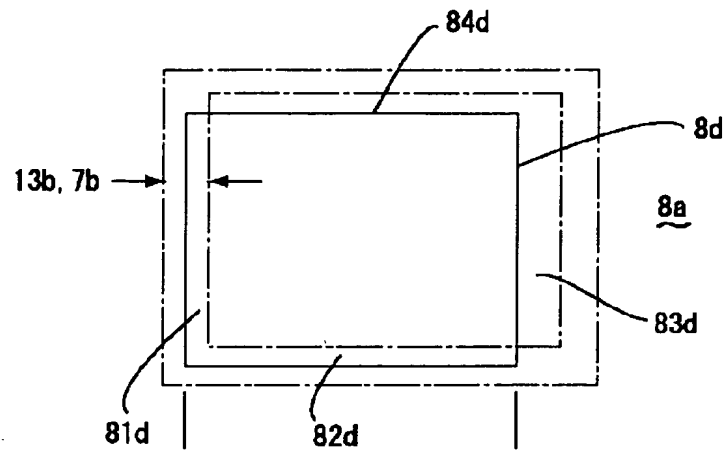


【FIG. 5】

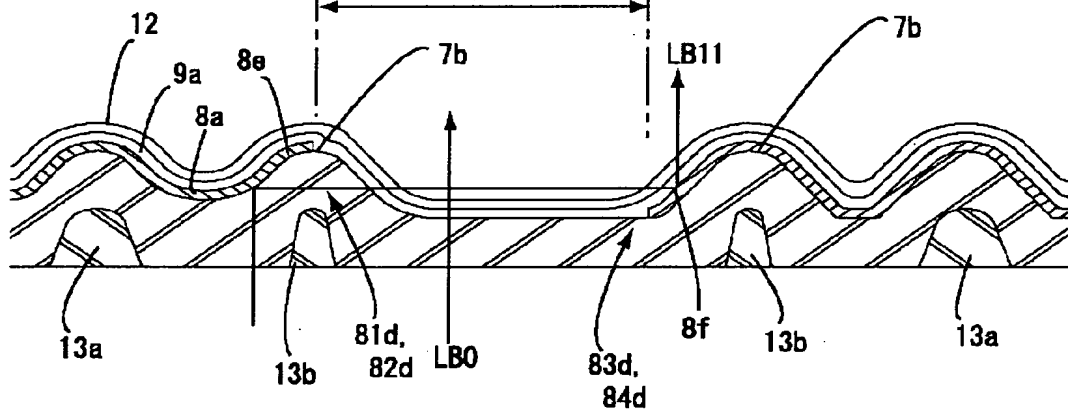


【FIG. 6】

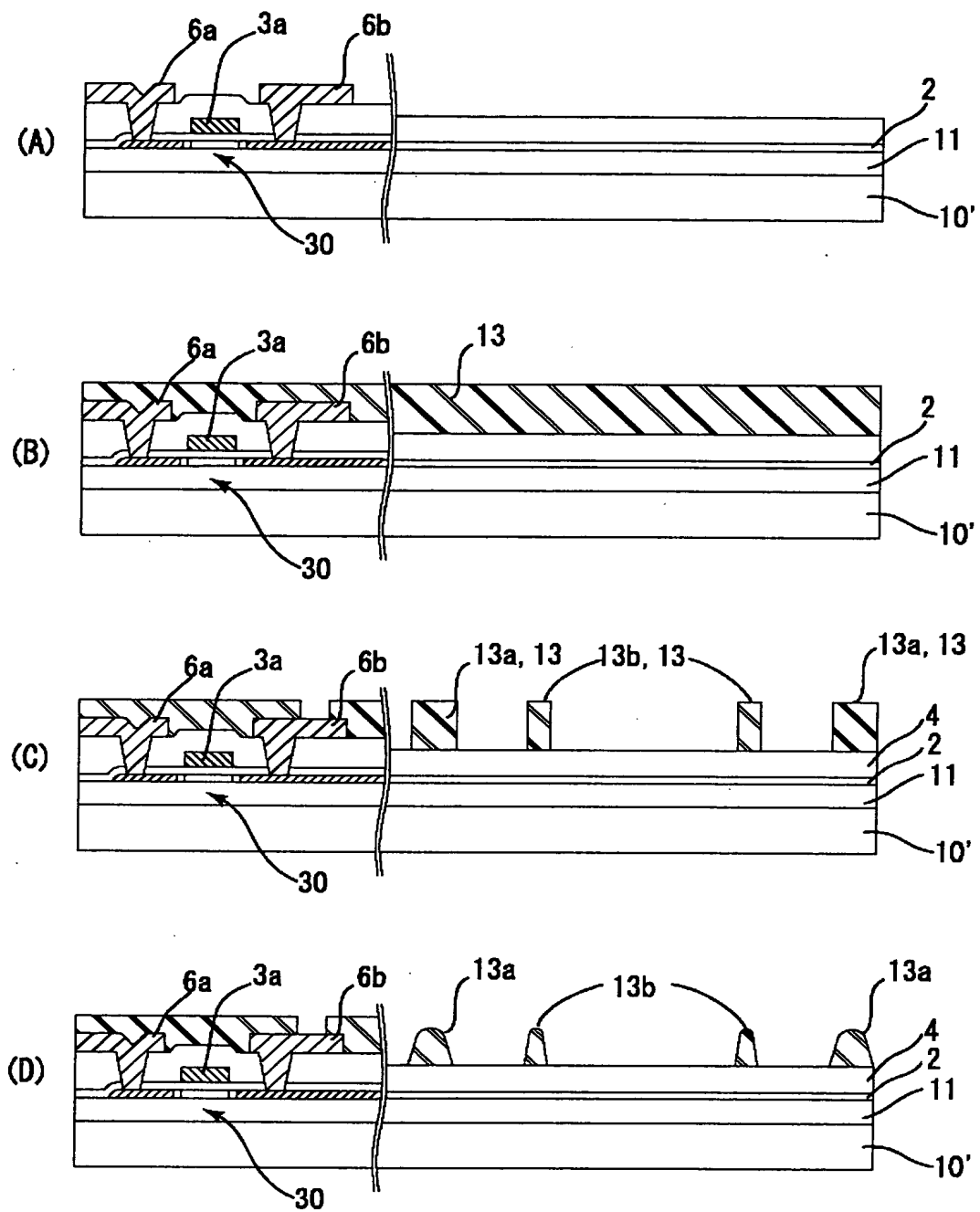
(A)



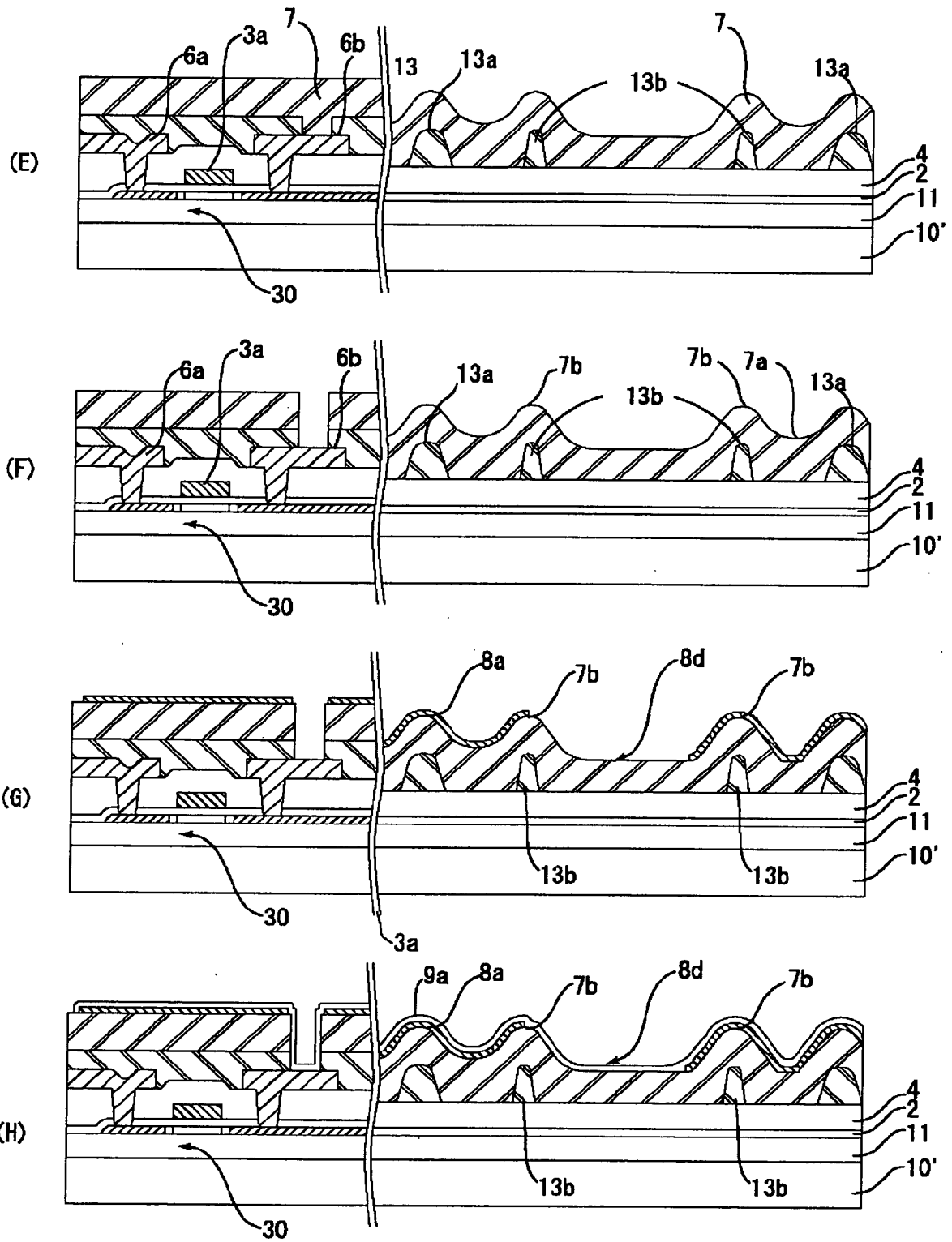
(B)



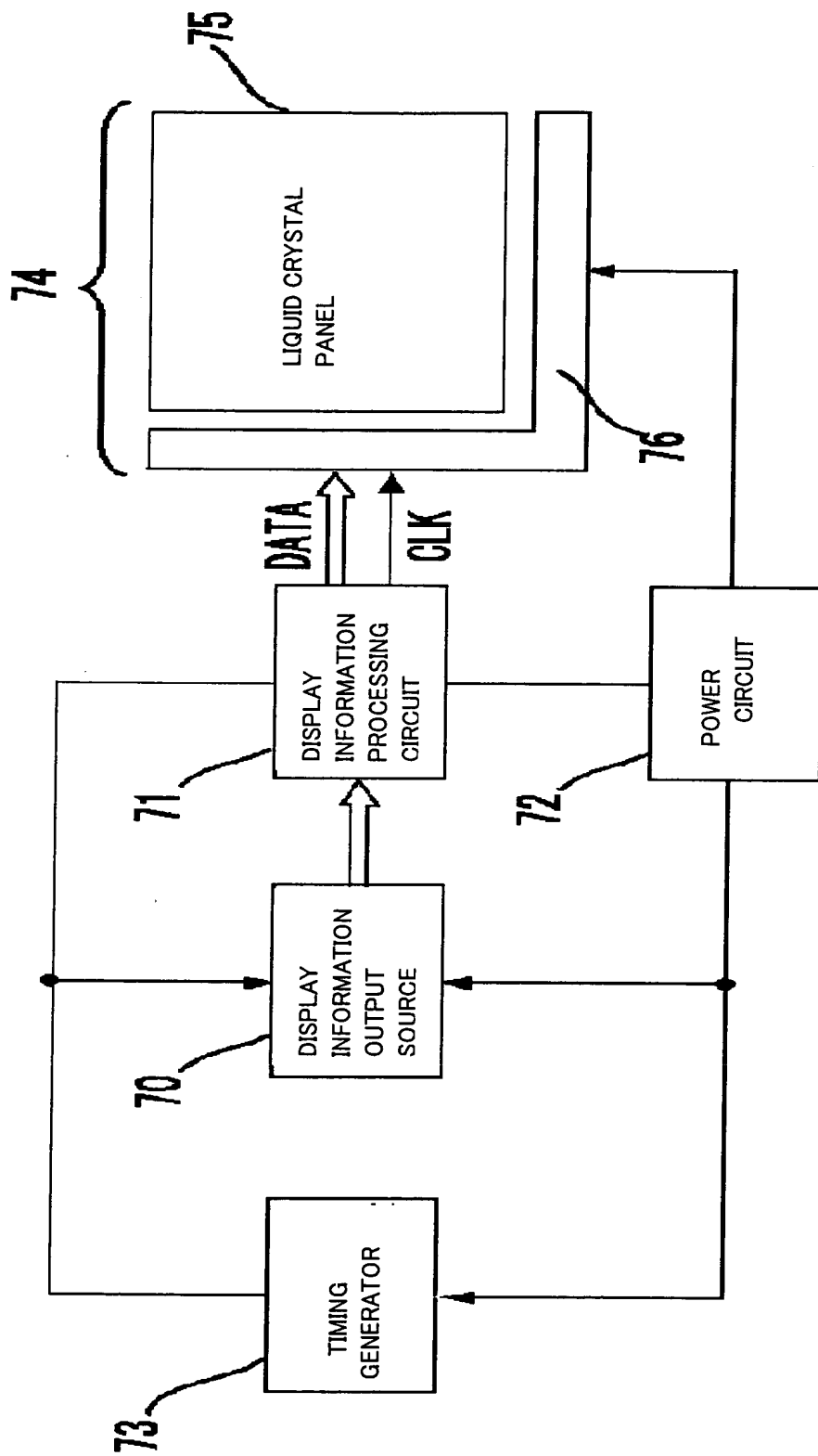
【FIG. 7】



【FIG. 8】

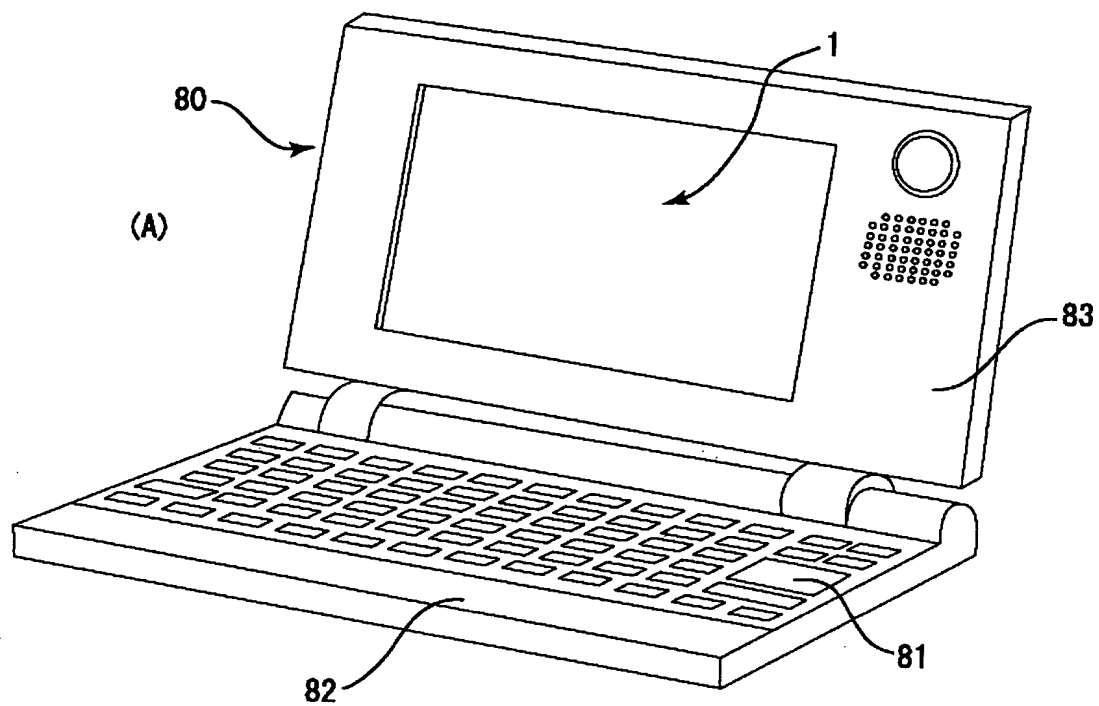


【FIG. 9】

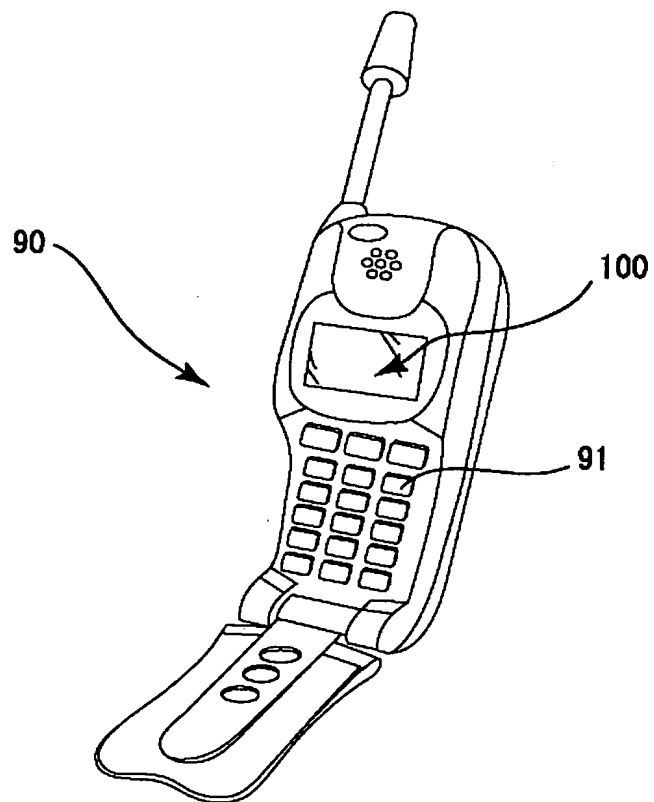




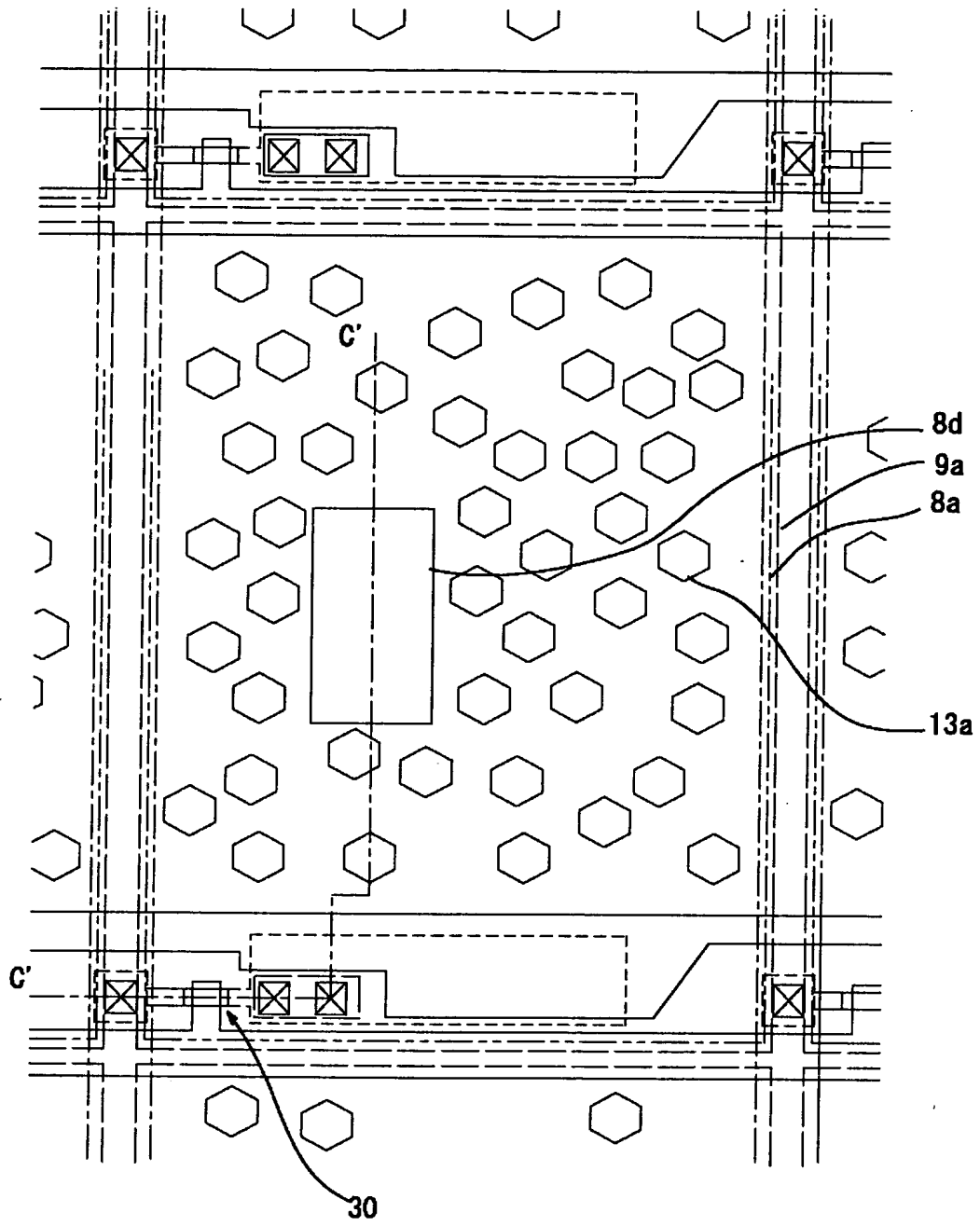
【FIG. 10】



(B)



【FIG. 11】



[illegible]

Diagram illustrating a cross-sectional view of a semiconductor device. The device consists of a substrate with a central region 7 and side regions 8a. A central layer 8d is shown with arrows LB1, LB0, and LB2 pointing to it. A vertical arrow LA points to a structure on the left side region 8a.